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Vishay Siliconix

# Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	40
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.006
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.008
I <sub>D</sub> (A)	32
Configuration	Single

#### **FEATURES**

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified<sup>d</sup>
- 100 % Rq and UIS Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912





COMPLIANT HALOGEN FREE

PowerPAK® SO-8L Single	D <b>O</b>
6,15 mm 5,13 mm	G
s s <sup>2</sup> s <sup>1</sup>	N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ884EP-T1-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> (T	$_{\rm C}$ = 25 °C, unles	s otherwise noted	l)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		$V_{DS}$	40		
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Currenta	T <sub>C</sub> = 25 °C	1	32		
Continuous Drain Current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	32		
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	32	Α		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	128		
Single Pulse Avalanche Current	1 0111	I <sub>AS</sub>	40		
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	80	mJ	
Maximum Dawar Dissination	T <sub>C</sub> = 25 °C 55	W			
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	18	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175		
Soldering Recommendations (Peak Temperature)e, f		-	260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	70	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	2.7	C/VV

#### **Notes**

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.
- e. See Solder Profile (www.vishay.com/doc?73257). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	1			ı		ı	ı
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> =	= 0 V, I <sub>D</sub> = 250 μA	40	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	150	-
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 13 A	-	0.0053	0.006	
Drain Cauras On State Resistance	В	V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 10 A	-	0.0060	0.008	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 13 A, T <sub>J</sub> = 125 °C	-	-	0.0088	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 13 A, T <sub>J</sub> = 175 °C	-	-	0.0107	
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 13 A		-	90	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	2368	2960	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 20 V, f = 1 MHz	-	360	450	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	]		-	140	175	
Total Gate Charge <sup>c</sup>	Qg			-	43	65	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, I_{D} = 20 \text{ A}$	-	7.5	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	]		-	7.1		
Gate Resistance	R <sub>g</sub>		f = 1 MHz	1.5	2.98	5	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	10	15	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$	= 20 V, $R_1 = 2 \Omega$	-	11	17	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	31	47	ns
Fall Time <sup>c</sup>	t <sub>f</sub>	1		-	8	12	
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	128	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	-	0.8	1.2	V	

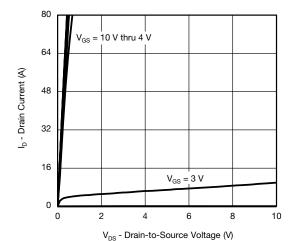
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

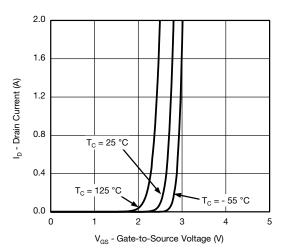
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



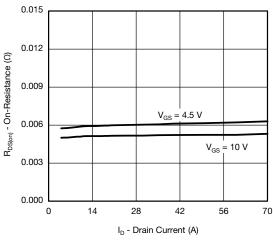
#### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



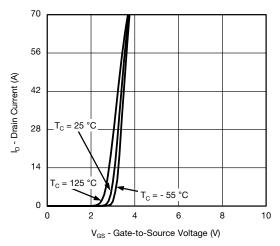
**Output Characteristics** 



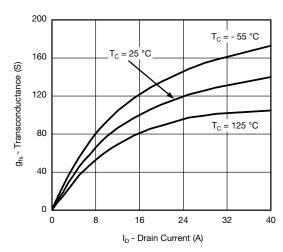
**Transfer Characteristics** 



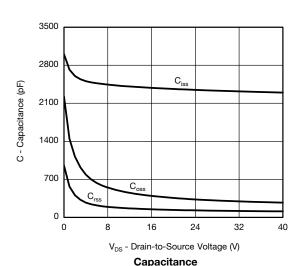
On-Resistance vs. Drain Current



**Transfer Characteristics** 

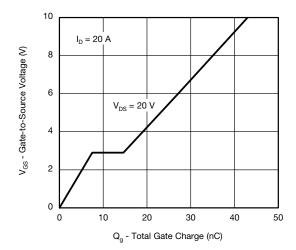


Transconductance

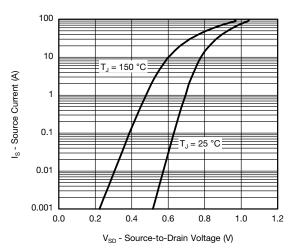




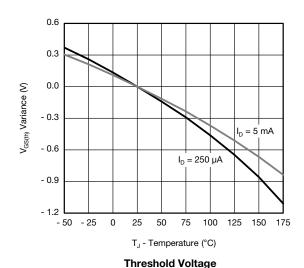
#### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

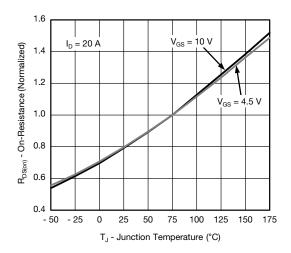


#### **Gate Charge**

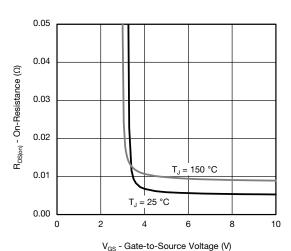


#### Source Drain Diode Forward Voltage

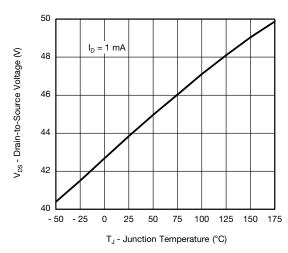




#### On-Resistance vs. Junction Temperature



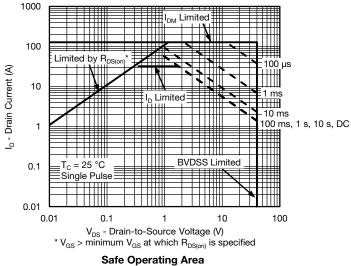
On-Resistance vs. Gate-to-Source Voltage

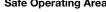


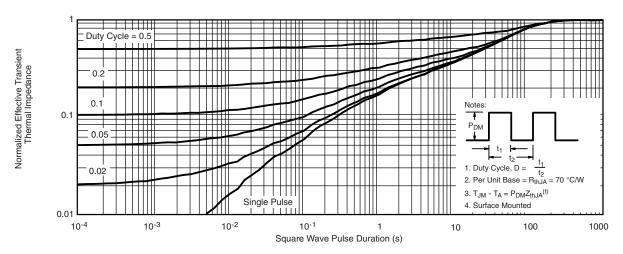
Drain Source Breakdown vs. Junction Temperature



### **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



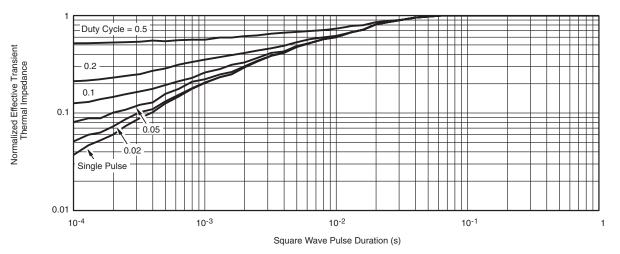




Normalized Thermal Transient Impedance, Junction-to-Ambient

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#### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

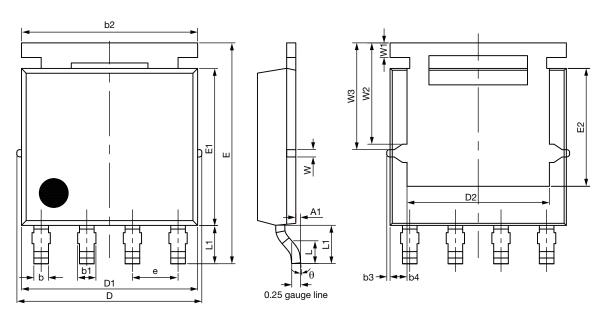
- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg267492">www.vishay.com/ppg267492</a>.

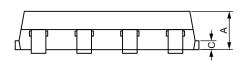
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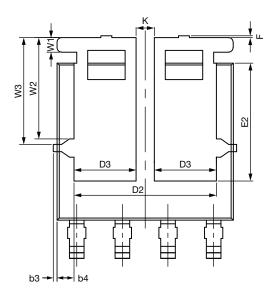
# PowerPAK® SO-8L Case Outline for Non-Al Parts



Topside view

Backside view (single)





Backside view (dual)





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DIM		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX	
Α	1.00	1.07	1.14	0.039	0.042	0.04	
A1	0.00	-	0.127	0.00	-	0.00	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.13	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W		0.23			0.009		
W1		0.41			0.016		
W2		2.82			0.111		
W3		2.96			0.117		
θ	0°	-	10°	0°	-	10°	

ECN: T16-0221-Rev. D, 16-May-16

DWG: 5976

#### Note

• Millimeters will gover



#### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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